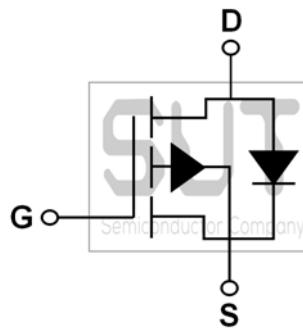
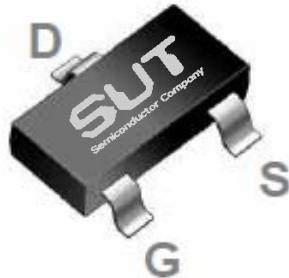


## P-Channel 20-V<sub>(D-S)</sub> MOSFET

PRODUCT SUMMARY		
B <sub>VDS</sub> (V)	R <sub>DS(on)</sub> (mΩ)(MAX)	I <sub>D</sub> (A)
-20	110@V <sub>GS</sub> =-4.5V	-3.2

### SOT23 Pin Configuration



### ABSOLUTE MAXIMUM RATINGS(T<sub>C</sub>=25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V <sub>DS</sub>	-20	V
Gate-Source Voltage	V <sub>GS</sub>	±8.0	V
Drain Current-Continuous (T <sub>C</sub> =25°C)	I <sub>D</sub>	-3.2	A
Drain Current-Continuous (T <sub>C</sub> =100°C)		-2.1	A
Drain Current-Pulsed <sup>1</sup>	I <sub>DM</sub>	-13.2	A
Power Dissipation (T <sub>C</sub> =25°C)	P <sub>D</sub>	1.56	W
Power Dissipation-Derate above 25°C		0.012	W/°C
Storage Temperature Range	T <sub>STG</sub>	-55 to 150	°C
Operating Junction Temperature Range	T <sub>J</sub>	-55 to 150	°C

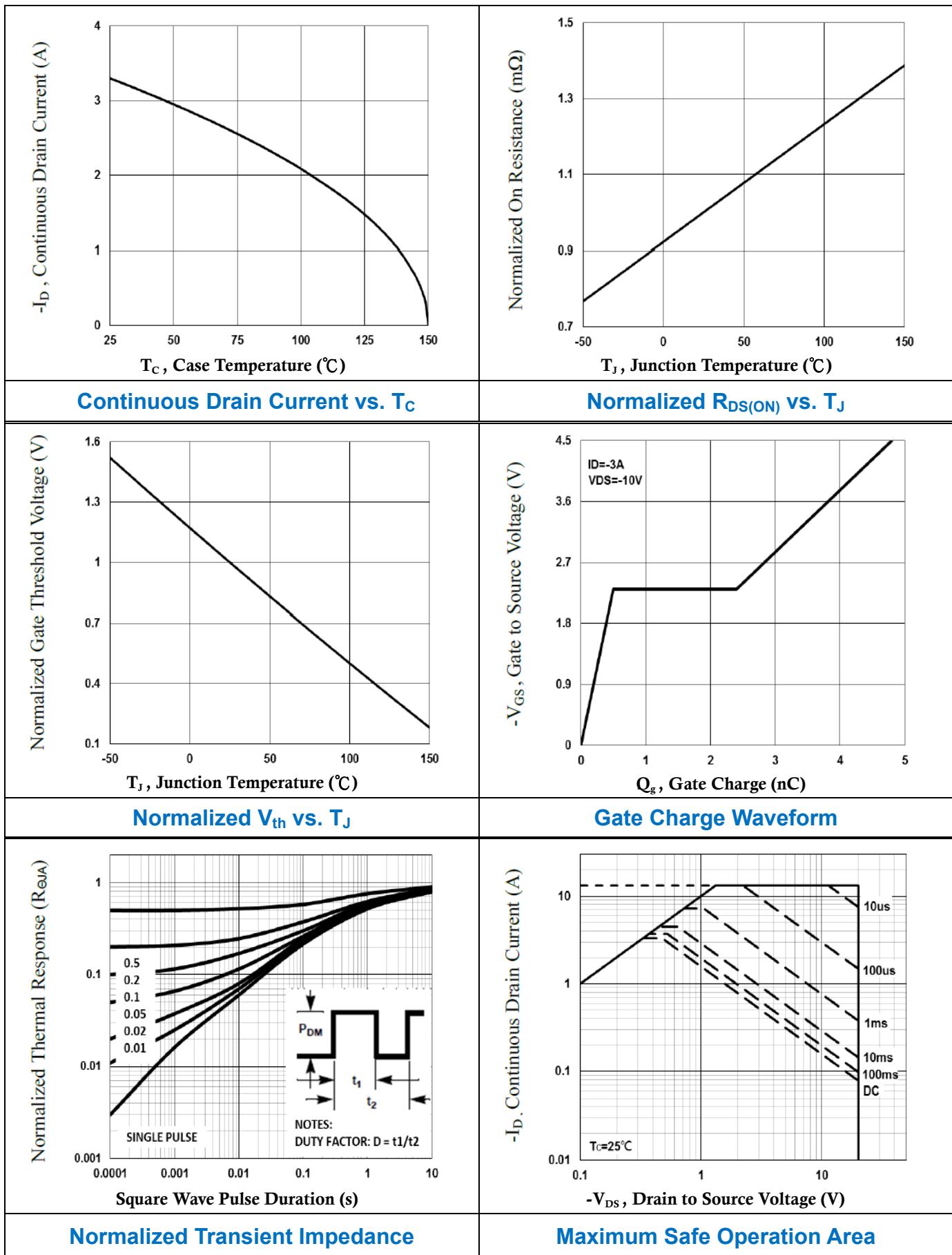
### THERMAL CHARACTERISTICS

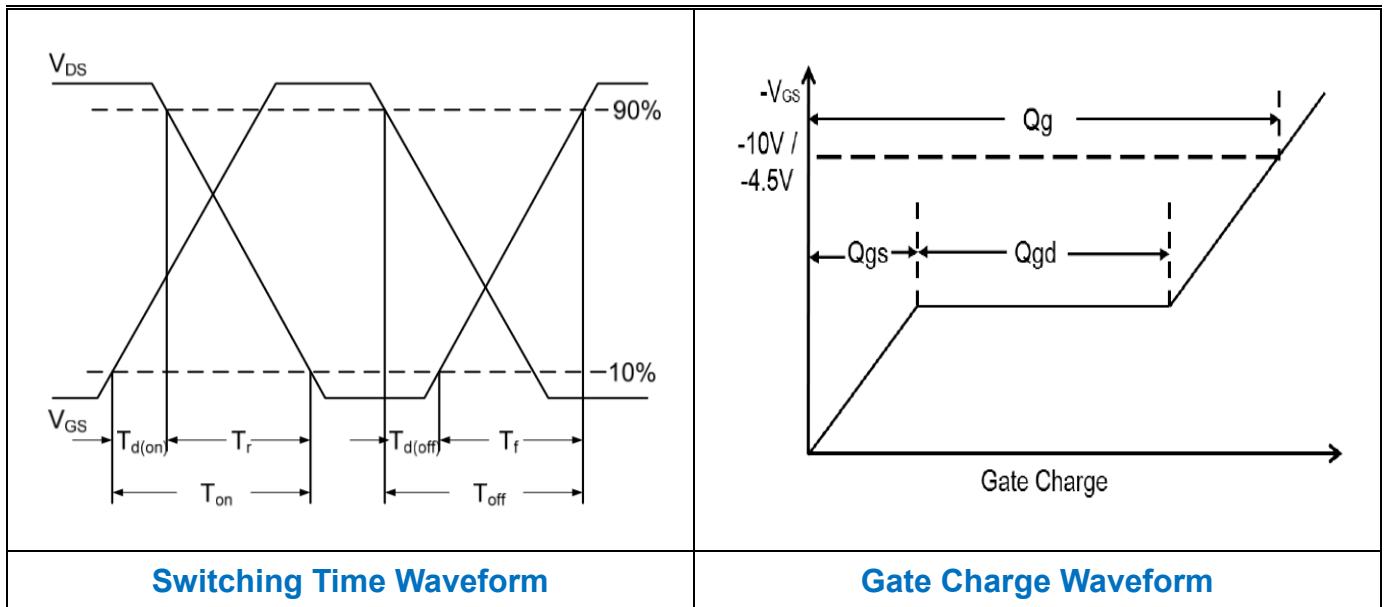
Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance Junction to ambient	R <sub>θJA</sub>	---	80	°C/W

ELECTRICAL CHARACTERISTICS ( $T_J=25^\circ\text{C}$ UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-20	---	---	V
$\text{BV}_{\text{DSS}}$ Temperature Coefficient	$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Reference to $25^\circ\text{C}, I_{\text{D}}=-1\text{mA}$	---	-0.01	---	$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	$I_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-20\text{V}, T_J=25^\circ\text{C}$	---	---	-1	$\mu\text{A}$
		$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-16\text{V}, T_J=125^\circ\text{C}$	---	---	-10	$\mu\text{A}$
Gate-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{DS}}=0\text{V}, V_{\text{GS}}=\pm 10\text{V}$	---	---	$\pm 100$	$\text{nA}$
<b>On Characteristics</b>						
Static Drain-Source On-Resistance	$R_{\text{DS(ON)}}$	$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-2.8\text{A}$	---	85	110	$\text{m}\Omega$
		$V_{\text{GS}}=-2.5\text{V}, I_{\text{D}}=-2\text{A}$	---	110	150	$\text{m}\Omega$
		$V_{\text{GS}}=-1.8\text{V}, I_{\text{D}}=-1\text{A}$	---	197	230	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{GS}}=V_{\text{DS}}, I_{\text{D}}=-250\mu\text{A}$	-0.5	-0.7	-1.4	V
$V_{\text{GS(th)}}$ Temperature Coefficient	$\Delta V_{\text{GS(th)}}$		---	3.0	---	$\text{mV}/^\circ\text{C}$
Forward Transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-1\text{A}$	---	2.2	---	S
<b>Dynamic and Switching Characteristics</b>						
Total Gate Charge <sup>2, 3</sup>	$Q_g$	$V_{\text{GS}}=-4.5\text{V}, V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-3\text{A}$	---	4.8	8.0	nC
Gate-Source Charge <sup>2, 3</sup>	$Q_{\text{gs}}$		---	0.5	1.0	
Gate-Drain Charge <sup>2, 3</sup>	$Q_{\text{gd}}$		---	1.9	4.0	
Turn-On Delay Time <sup>2, 3</sup>	$T_{\text{d(on)}}$	$V_{\text{GS}}=-4.5\text{V}, V_{\text{DD}}=-10\text{V}, R_{\text{G}}=25\Omega, I_{\text{D}}=-1\text{A}$	---	3.5	7.0	ns
Rise Time <sup>2, 3</sup>	$T_r$		---	12.6	24	
Turn-Off Delay Time <sup>2, 3</sup>	$T_{\text{d(off)}}$		---	32.6	62	
Fall Time <sup>2, 3</sup>	$T_f$		---	8.4	16	
Input Capacitance	$C_{\text{iss}}$	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=-15\text{V}, F=1\text{MHz}$	---	350	510	pF
Output Capacitance	$C_{\text{oss}}$		---	65	95	
Reverse Transfer Capacitance	$C_{\text{rss}}$		---	50	75	
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Continuous Source Current	$I_s$	$V_G=V_D=0\text{V}$ , Force Current	---	---	-3.2	A
Pulsed Source Current	$I_{\text{SM}}$		---	---	-12.8	A
Diode Forward Voltage	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_s=-1\text{A}, T_J=25^\circ\text{C}$	---	---	-1.0	V

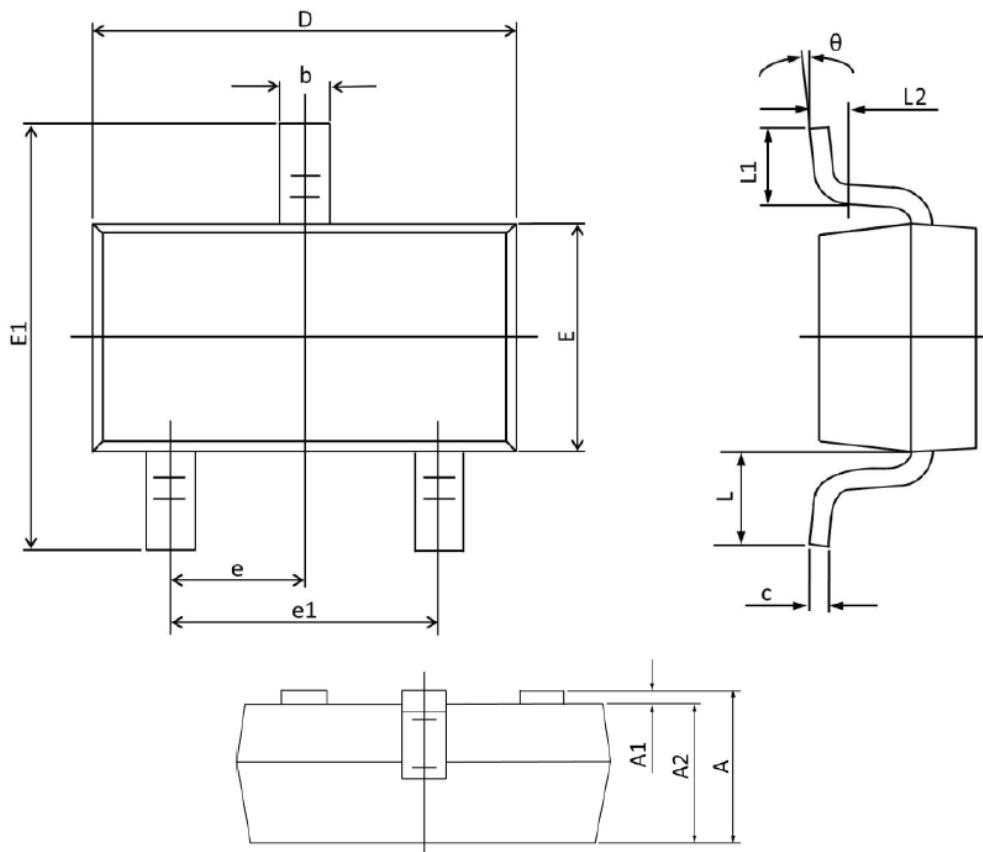
Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width  $\leq 300\text{us}$  , duty cycle  $\leq 2\%$ .
3. Essentially independent of operating temperature.





## SOT23 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MAX	MIN	MAX	MIN
A	1.150	0.900	0.045	0.035
A1	0.100	0.000	0.004	0.000
A2	1.050	0.900	0.041	0.035
b	0.500	0.300	0.020	0.012
c	0.150	0.080	0.006	0.003
D	3.000	2.800	0.118	0.110
E	1.400	1.200	0.055	0.047
E1	2.550	2.250	0.100	0.089
e	0.950(TYP)		0.037(TYP)	
e1	2.000	1.800	0.079	0.071
L	0.550(REF)		0.022(REF)	
L1	0.500	0.300	0.020	0.012
L2	0.250(TYP)		0.010(TYP)	
θ	8°	0°	8°	0°